

IN THE CLAIMS:

Subt F¹ ✓ Please amend claims 25, 28 and 31 as follows:

E1 5 25. (Four Times Amended) A semiconductor device comprising:
a semiconductor substrate;
an interlayer insulating film located on the semiconductor substrate;
wirings located on the interlayer insulating film; and
a passivation film covering the surface of the interlayer insulating film and the wirings, including a first insulating film that is a modified spin-on-glass (SOG) film containing boron impurity implanted into an organic SOG film to form the modified SOG film.

Subt F² ✓ *E2* 28. (Twice Amended) The semiconductor device according to claim 25, wherein the first insulating film includes organic components decomposed by said boron impurity.

Subt F³ ✓ *E3* 5 31. (Four Times Amended) A semiconductor device comprising:
a semiconductor substrate;
an interlayer insulating film located on the semiconductor substrate;
wirings located on the interlayer insulating film; and
a passivation film covering the surface of the interlayer insulating film and the wirings, including a first insulating film that is a modified spin-on-glass (SOG) film containing boron impurity implanted into an inorganic SOG film to form the modified SOG film.